

22/151

B.Sc. (Part-III) Examination, 2022

PHYSICS

Third Paper

(Solid State Electronics)

Time : Three Hours ] [ Maximum Marks : 75

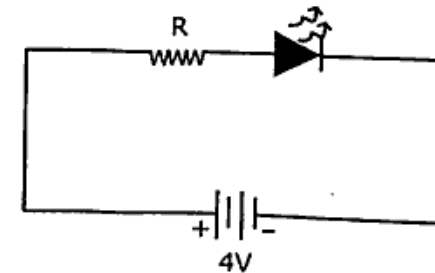
**Note :** Attempt questions from **all** sections as per instructions.

Section - A  $1\frac{1}{2} \times 10 = 15$ 

1. (i) What is junction breakdown? What are the causes of Avalanche and Zener breakdowns?
- (ii) Plot the variations of charge density electric potential and the electric field across p-n junction, within the depletion layer.

P.T.O.

- (iii) Explain why the light emitted from LED is incoherent? (2)
- (iv) Discuss the effect of increasing negative Gate Voltage on drain current of an n-channel JFET.
- (v) State the effect of temperature on the built-in Voltage. A Silicon diode has  $V_0 = 0.7$  Volt at  $25^\circ\text{C}$ . Find  $V_0$  when junction temperature is raised to  $100^\circ\text{C}$ .
- (vi) In the circuit, find R that keeps the LED safe:



- (vii) Explain Early effect.
- (viii) What is the advantage of phototransistor over photodiode?

22/151

(3)

- (ix) What is the basic difference between DMOSFET and EMOSFET? Draw their symbols.
- (x) What do you mean by regulation? Define Load and line regulations.

**Section - B**  $8 \times 5 = 40$

2. Explain, with neat diagram, how a potential barrier develops across a p-n junction.

A silicon p-n junction diode has  $N_A = 10^{17}$  atoms/cm<sup>3</sup>,  $N_D = 10^{15}$  atoms/cm<sup>3</sup>. For Silicon,  $n_i = 1 \times 10^{10}$ /cm<sup>3</sup>. Calculate the internal potential barrier at 300K.

**OR**

Derive the expression for the depletion (junction) capacitance of a p-n junction.

Plot C against bias voltage  $V_a$ .

22/151

P.T.O.

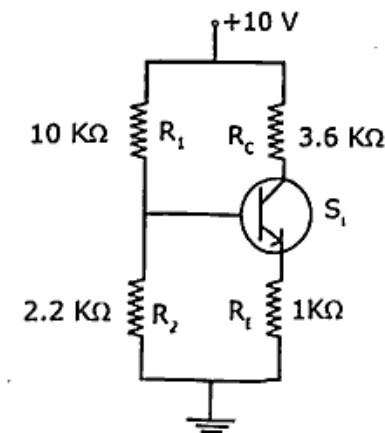
(4)

3. With the help of energy band diagram explain work function in metal and semiconductor. Explain how metal-semiconductor junctions achieve rectifying property. Compare V-I characteristic of Schottky barrier diode with that of p-n junction diode.

**OR**

Why do transistor amplifier circuits need biasing? Discuss the factors that may cause a shift in Q-point.

4. Determine the Q-point of the circuit



22/151

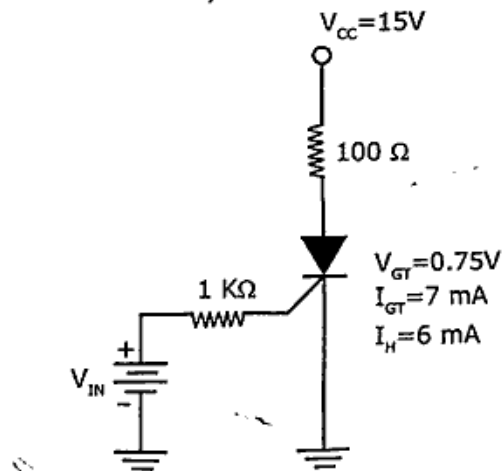
(5)  
OR

What is meant by Power Amplifier? Develop the expression for the maximum efficiency of a class B power amplifier.

5. With the help of 2-transistor model of SCR, explain how an SCR is turned on and OFF.

OR

In the SCR circuit,



Determine-

- Input voltage  $V_{IN}$  that triggers SCR.
- The supply voltage that turns SCR OFF

- (6)
6. What are chief sections of a regulated Power Supply. Draw circuit diagram of a Zener regulated Power Supply and discuss the functions of each component.

OR

Discuss briefly the basic construction, operation and characteristics of an n-channel Enhancement MOSFET.

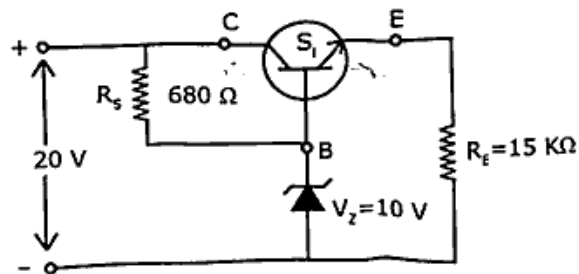
Section - C 10×2=20

7. Draw hybrid equivalent circuit of a CE transistor amplifier and hence obtain expressions for-
- Current gain
  - Input impedance and
  - Voltage gain

(7)

8. Derive the expression for the width of depletion layer  $W_0$  in terms of built-in voltage  $V_0$  and doping densities  $N_A$  and  $N_D$ .
9. Find the stability factor of an Emitter resistor and Potential Divider Bias transistor amplifier circuit. Discuss its advantages over other biasing methods.

10. In the pass-transistor regulator ,



Find (a) D.C. output voltage

(b) Zener current, if  $\beta=100$ .

(8)

11. Write short notes on any **two** :
- (a) Photodiodes and their applications
  - (b) Distortions in amplifiers.
  - (c) Transistor amplifiers and their D.C. and A.C. equivalent ckts.
  - (d) UJT and its applications.

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